Amendments to the Claims:

Please cancel Claims 1-9 and 19-24.

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-9 (canceled)

Claim 10 (original): A method of manufacturing a semiconductor device, comprising:

implanting source and drain regions having similar doping profiles in a semiconductor substrate, thereby defining a channel region extending from said source region to said drain region;

locating a dielectric layer over said source and drain regions, said dielectric layer having first and second thicknesses wherein said second thickness is substantially less than said first thickness and is partially located over said channel region; and

forming a gate over said dielectric layer wherein said second thickness is located between an end of said gate and one of said source and drain regions.

Claim 11 (original): The method recited in Claim 10 wherein said implanting includes implanting said source and drain regions simultaneously.

Claim 12 (original): The method recited in Claim 10 wherein said first thickness ranges between about 25 nm to about 50 nm.

Claim 13 (original): The method recited in Claim 10 wherein said second thickness ranges between about 6 nm and about 20 nm.

Claim 14 (original): The method recited in Claim 10 wherein said locating includes forming an interface between first and second layers of said dielectric layer.

Claim 15 (original): The method recited in Claim 10 wherein said implanting includes implanting said source and drain regions to a concentration of about 1.0E20 atoms/cm^3.

Claim 16 (original): The method recited in Claim 10 wherein said implanting includes implanting a lightly doped region in each of said source and drain regions, wherein said end of said gate and said second thickness are located over one of said lightly doped regions.

Claim 17 (original): The method recited in Claim 16 wherein said implanting said lightly doped region includes implanting to a concentration ranging between about 1.0E17 atoms/cm^3 and about 1.0E18 atoms/cm^3.

Claim 18 (original): The method recited in Claim 10 wherein said gate is a floating gate and further including forming a control gate over said floating gate.

Claims 19-24 (canceled)

Amendments to the Drawings:

None